## **Features**

- Low-voltage and Standard-voltage Operation
  - $-5.0 (V_{CC} = 4.5V \text{ to } 5.5V)$
  - $-2.7 (V_{CC} = 2.7V \text{ to } 5.5V)$
- Internally Organized 65,536 x 8
- 2-wire Serial Interface
- Schmitt Triggers, Filtered Inputs for Noise Suppression
- Bi-directional Data Transfer Protocol
- 1 MHz (5V) and 400 kHz (2.7V) Compatibility
- 128-byte Page Write Mode (Partial Page Writes Allowed)
- Self-timed Write Cycle (5 ms Typical)
- High Reliability
  - Endurance: 100,000 Write Cycles
  - Data Retention: 40 YearsESD Protection: >4000V

## **Description**

The AT24C512SC provides 524,288 bits of serial electrically erasable and programmable read only memory (EEPROM) organized as 65,536 words of 8 bits each. This device is optimized for use in smart card applications where low-power and low-voltage operation may be essential. This device is available in a standard ISO 7816 smart card module (see Ordering Information). The entire family is available in both high-voltage (4.5V to 5.5V) and low-voltage (2.7V to 5.5V) versions. All devices are functionally equivalent to Atmel Serial EEPROM products offered in standard IC packages (PDIP, SOIC, EIAJ, LAP), with the exception of the slave address and write protect functions which are not required for smart card applications.

# **Pin Configurations**

Pad Name	Description	ISO Module Contact
VCC	Power Supply Voltage	C1
GND	Ground	C5
SCL	Serial Clock Input	C3
SDA	Serial Data Input/Output	C7
NC	No Connect	C2, C4, C6, C8

## **Card Module Contact**

VCC = C1		C5 = GND
NC = C2		C6 = NC
SCL = C3		C7 = SDA
NC = C4		C8 = NC



# 2-wire Serial EEPROM Smart Card Module

512K (65,536 x 8)

# **AT24C512SC**

# **Preliminary**







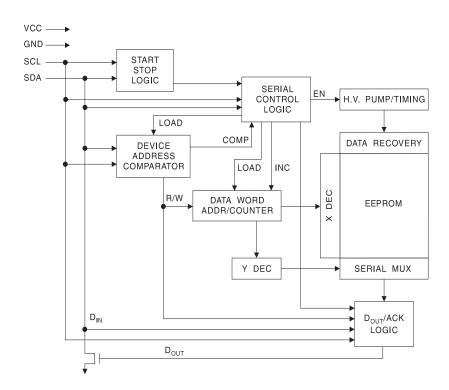
## **Absolute Maximum Ratings\***

Operating Temperature55°C to +125°C
Storage Temperature65°C to +150°C
Voltage on Any Pin with Respect to Ground1.0V to +7.0V
Maximum Operating Voltage
DC Output Current

#### \*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **Block Diagram**



# **Pin Description**

**SERIAL CLOCK (SCL):** The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

**SERIAL DATA (SDA):** The SDA pin is bidirectional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open collector devices.

# **Memory Organization**

**AT24C512SC**, **512K SERIAL EEPROM**: The 512K is internally organized as 512 pages of 128 bytes each. Random word addressing requires a 16-bit data word address.

# Pin Capacitance<sup>(1)</sup>

Applicable over recommended operating range from  $T_A = 25^{\circ}C$ , f = 1.0 MHz,  $V_{CC} = +2.7V$ .

Symbol Test Condition		Max	Units	Conditions
C <sub>I/O</sub>	Input/Output Capacitance (SDA)	8	pF	$V_{I/O} = 0V$
C <sub>IN</sub>	Input Capacitance (SCL)	6	pF	V <sub>IN</sub> = 0V

Note: 1. This parameter is characterized and is not 100% tested.

## **DC Characteristics**

Applicable over recommended operating range from:  $T_{AC} = 0^{\circ}C$  to  $+70^{\circ}C$ ,  $V_{CC} = +2.7V$  to +5.5V (unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Тур	Max	Units
V <sub>CC1</sub>	Supply Voltage			2.7		5.5	V
V <sub>CC2</sub>	Supply Voltage			4.5		5.5	V
I <sub>CC1</sub>	Supply Current	V <sub>CC</sub> = 5.0V	Read at 400 kHz		1.0	2.0	mA
I <sub>CC2</sub>	Supply Current	V <sub>CC</sub> = 5.0V	Write at 400 kHz		2.0	3.0	mA
	Standby Current	V <sub>CC</sub> = 2.7V	V V OND			0.6	μΑ
I <sub>SB1</sub>	(2.7V option)	V <sub>CC</sub> = 5.5V	$V_{IN} = V_{CC}$ or GND			6.0	
I <sub>SB2</sub>	Standby Current (5.0V option)	V <sub>CC</sub> = 4.5 - 5.5V	V <sub>IN</sub> = V <sub>CC</sub> or GND			6.0	μΑ
I <sub>LI</sub>	Input Leakage Current	V <sub>IN</sub> = V <sub>CC</sub> or GND			0.10	3.0	μΑ
I <sub>LO</sub>	Output Leakage Current	V <sub>OUT</sub> = V <sub>CC</sub> or GND			0.05	3.0	μΑ
V <sub>IL</sub>	Input Low Level <sup>(1)</sup>			-0.6		V <sub>CC</sub> x 0.3	V
V <sub>IH</sub>	Input High Level <sup>(1)</sup>			V <sub>CC</sub> x 0.7		V <sub>CC</sub> + 0.5	V
V <sub>OL</sub>	Output Low Level	V <sub>CC</sub> = 3.0V I <sub>OL</sub> = 2.1 mA				0.4	V

Note: 1.  $V_{IL}$  min and  $V_{IH}$  max are reference only and are not tested.





### AC Characteristics

Applicable over recommended operating range from  $T_A = 0$ °C to +70°C,  $V_{CC} = +2.7$ V to +5.5V,  $C_L = 100$  pF (unless otherwise noted). Test conditions are listed in Note 2.

		2.7-	2.7-volt		volt	
Symbol	Parameter	Min	Max	Min	Max	Units
f <sub>SCL</sub>	Clock Frequency, SCL		400		1000	kHz
$t_{LOW}$	Clock Pulse Width Low	1.3		0.6		μs
t <sub>HIGH</sub>	Clock Pulse Width High	1.0		0.4		μs
t <sub>AA</sub>	Clock Low to Data Out Valid	0.05	0.9	0.05	0.55	μs
t <sub>BUF</sub>	Time the bus must be free before a new transmission can start <sup>(1)</sup>	1.3		0.5		μѕ
t <sub>HD.STA</sub>	Start Hold Time	0.6		0.25		μs
t <sub>SU.STA</sub>	Start Set-up Time	0.6		0.25		μs
t <sub>HD.DAT</sub>	Data In Hold Time	0		0		μs
t <sub>SU.DAT</sub>	Data In Set-up Time	100		100		ns
t <sub>R</sub>	Inputs Rise Time <sup>(1)</sup>		0.3		0.3	μs
t <sub>F</sub>	Inputs Fall Time <sup>(1)</sup>		300		100	ns
t <sub>su.sto</sub>	Stop Set-up Time	0.6		0.25		μs
t <sub>DH</sub>	Data Out Hold Time	50		50		ns
t <sub>WR</sub>	Write Cycle Time		10		10	ms
Endurance <sup>(1)</sup>	5.0V, 25°C, Page Mode	100K		100K		Write Cycles

- Notes: 1. This parameter is characterized and is not 100% tested.
  - 2. AC measurement conditions:

 $R_L$  (connects to  $V_{CC}$ ): 1.3 k $\Omega$  (2.7V, 5V) Input pulse voltages: 0.3V<sub>CC</sub> to 0.7V<sub>CC</sub> Input rise and fall times: ≤ 50ns

Input and output timing reference voltages: 0.5V<sub>CC</sub>

# **Device Operation**

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (refer to Data Validity timing diagram). Data changes during SCL high periods will indicate a start or stop condition as defined below.

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (refer to Start and Stop Definition timing diagram).

**STOP CONDITION:** A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (refer to Start and Stop Definition timing diagram).

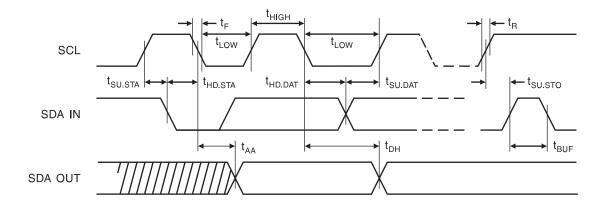
ACKNOWLEDGE: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a zero during the ninth clock cycle to acknowledge that it has received each word.

STANDBY MODE: The AT24C512SC features a low power standby mode which is enabled: a) upon power-up and b) after the receipt of the STOP bit and the completion of any internal operations.

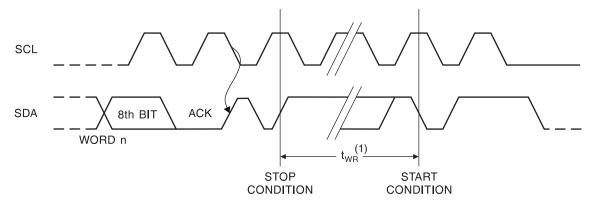
**MEMORY RESET:** After an interruption in protocol, power loss or system reset, any 2-wire part can be reset by following these steps:

- 1. Clock up to 9 cycles.
- 2. Look for SDA high in each cycle while SCL is high.
- 3. Create a start condition as SDA is high.

# Bus Timing (SCL: Serial Clock, SDA: Serial Data I/O)



# Write Cycle Timing (SCL: Serial Clock, SDA: Serial Data I/O)

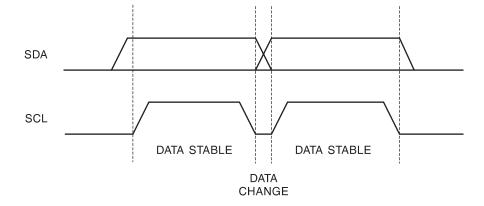


Note: 1. The write cycle time t<sub>WR</sub> is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

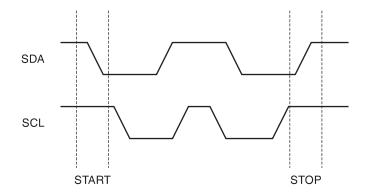




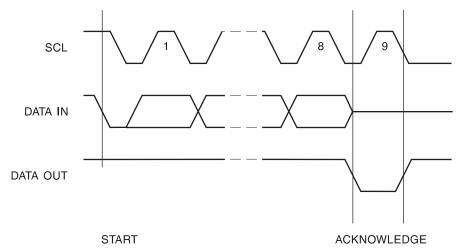
# **Data Validity**



# **Start and Stop Definition**



# **Output Acknowledge**



## **Device Addressing**

The 512K EEPROM requires an 8-bit device address word following a start condition to enable the chip for a read or write operation (refer to Figure 1). The device address word consists of a mandatory one, zero sequence for the first four most significant bits as shown. This is common to all 2-wire EEPROM devices.

The next three bits of the device address word are unused. These three unused bits should be set to "0".

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the device will return to a standby state.

## **Write Operations**

BYTE WRITE: A write operation requires two 8-bit data word addresses following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero. The addressing device, such as a microcontroller, then must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally-timed write cycle,  $t_{WR}$ , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (refer to Figure 2).

**PAGE WRITE:** The 512K EEPROM is capable of 128-byte page writes.

A page write is initiated the same way as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 127 more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a stop condition (refer to Figure 3).

The data word address lower seven bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 128 data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten. The address "roll over" during write is from the last byte of the current page to the first byte of the same page.

**ACKNOWLEDGE POLLING:** Once the internally-timed write cycle has started and the EEPROM inputs are dis-

abled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero, allowing the read or write sequence to continue.

## **Read Operations**

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to one. There are three read operations: current address read, random address read and sequential read.

**CURRENT ADDRESS READ:** The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page, to the first byte of the first page.

Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition (refer to Figure 4).

RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition (refer to Figure 5).

**SEQUENTIAL READ:** Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a zero but does generate a following stop condition (refer to Figure 6).





Figure 1. Device Address

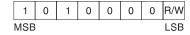


Figure 2. Byte Write

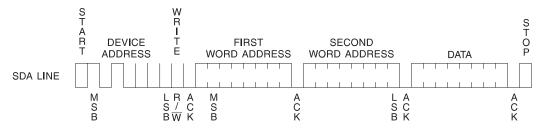


Figure 3. Page Write

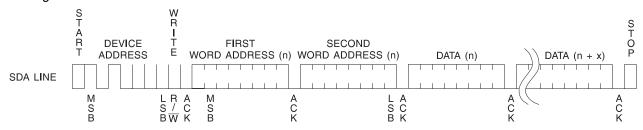


Figure 4. Current Address Read

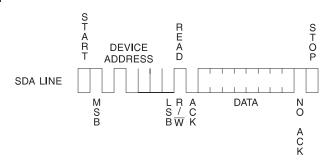


Figure 5. Random Read

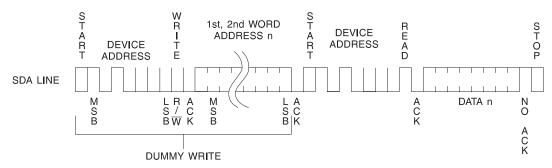
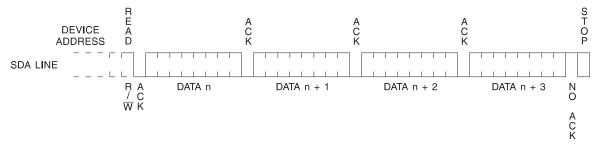


Figure 6. Sequential Read







# **AT24C32SC Ordering Information**

Ordering Code	Package <sup>(1)</sup>	Voltage Range	Temperature Range
AT24C512SC - 09AT - 2.7	M2 - L Module	2.7V to 5.5V	Commercial (0°C to 70°C)
AT24C512SC - 09AT	M2 - L Module	4.5V to 5.5V	Commercial (0°C to 70°C)

Package Type <sup>(1)</sup>	
M2 - L Module	M2 ISO 7816 Smart Card Module

Notes: 1. Formal drawings may be obtained from an Atmel Sales Office.

2. Atmel currently offers this device in the "L" module only.

## **Smart Card Module**

M2 - L Module - Ordering code: 09LT



Module Size: M2

Dimension<sup>(1)</sup>: 12.6 x 11.4 [mm] Glob Top: Square: 8.6 x 8.6 [mm]

Thickness: 0.58 [mm] max.

Pitch: 14.25 mm

Note: 1. The module dimensions listed refer to the

dimensions of the exposed metal contact area. The actual dimensions of the module after excise or punching from the carrier tape are generally 0.4 mm greater in both directions (i.e. a punched M2 module

will yield 13.0 x 11.8 mm).





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